

STD724

NPN MEDIUM POWER TRANSISTORS

Features

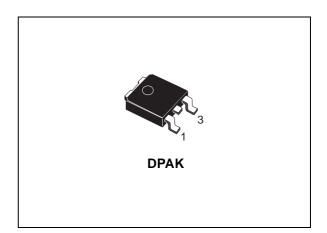
- SURFACE MOUNTING DEVICE IN MEDIUM POWER DPAK POWER PACKAGE
- AVAILABLE IN TAPE & REEL PACKING
- IN COMPLIANCE WITH THE 2002/93/EC EUROPEAN DIRECTIVE

Applications

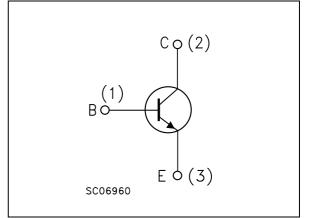
- VOLTAGE REGULATION
- RELAY DRIVER
- GENERIC SWITCH

Description

The device is a NPN transistor manufactured using planar Technology resulting in rugged high performance devices.



Internal Schematic Diagram



Order codes

Part Number	Marking	Package	Packing
STD724T4	D724	DPAK	Tape & reel

1 Electrical Ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	60	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	30	V
V_{EBO}	Collector-Base Voltage ($I_C = 0$)	5	V
۱ _C	Collector Current	3	А
I _{CM}	Collector Peak Current (t _P < 5ms)	6	А
Ι _Β	ase Current 1		А
I _{BM}	Base Peak Current (t _P < 5ms)	2	А
P _{TOT}	Total dissipation at $T_c = 25^{\circ}C$	15	W
T _{STG}	Storage Temperature -65 to 150		°C
Τ _J	Max. Operating Junction Temperature	150	

Table 1. Absolute Maximum Rating

Table 2. Thermal Data

Symbol	Parameter	Value	Unit
R _{thj-amb}	Thermal Resistance Junction-Amb Max	8.33	°C/W



2 Electrical Characteristics

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 60V				10	μΑ
I _{CEO}	Collector Cut-off Current $(I_B = 0)$	V _{CE} = 30V				100	μΑ
I _{EBO}	Emitter Cut-off Current $(I_{C} = 0)$	V _{EB} = 5V				10	μA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = 100μA		60			V
V _{(BR)CEO} Note 1	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = 10 mA		30			V
V _{(BR)EBO}	Collector-Emitter Breakdown Voltage (I _C = 0)	I _E = 100 μA		5			V
V _{CE(sat)} Note 1	Collector-Emitter Saturation Voltage	$I_{C} = 1 A$ $I_{C} = 2 A$ $I_{C} = 3 A$	I _B = 50 mA I _B = 100 mA I _B = 150 mA			0.4 0.7 1.1	V V V
V _{BE(sat)} Note 1	Base-Emitter Saturation Voltage	I _C = 2 A	I _B = 100 mA			1.2	V
h _{FE}	DC Current Gain	$I_{C} = 100 \text{ mA}$ $I_{C} = 1 \text{ A}$ $I_{C} = 3 \text{ A}$	$V_{CE} = 2 V$ $V_{CE} = 2 V$ $V_{CE} = 2 V$	100 80 30		300	
f _T	Transistor Frequency	V _{CE} = 10 V	I _c = 0.1 A		100		MHz

Table 3.Electrical Characteristics ($T_{CASE} = 25^{\circ}C$; unless otherwise specified)

1 Pulsed duration = 300 μ s, duty cycle \leq 1.5%.



2.1 Electrical characteristics (curve)

Figure 1. DC Current Gain

Figure 2. DC Current Gain

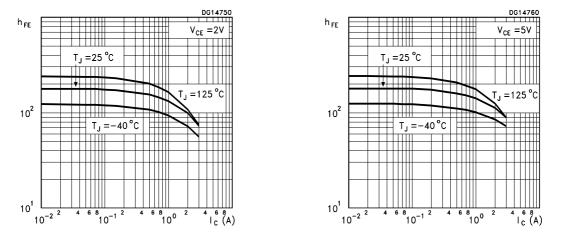
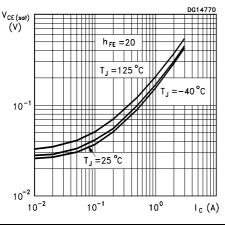
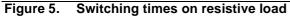
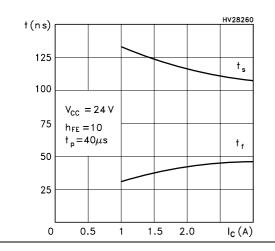


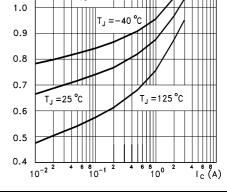
Figure 3. Collector-emitter saturation voltage Figure 4. Base-emitter saturation voltage

V_{BE(sat)} (V)









h _{FE} =20

Figure 6. Switching times resistive on load

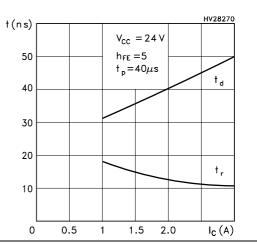
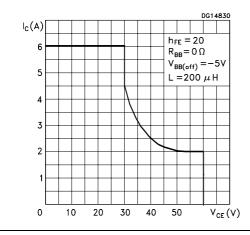




Figure 7. Reverse biased area





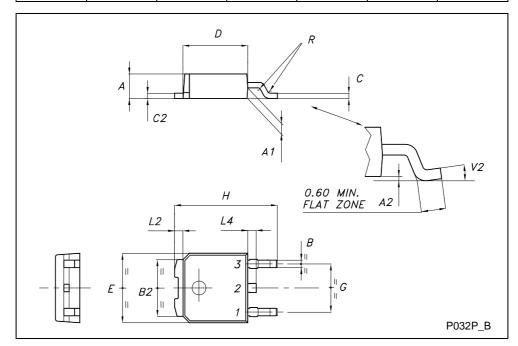
3 Package Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

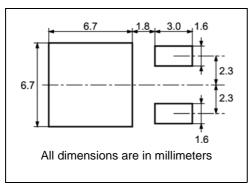


DIM.	M. mm MIN. TYP. MAX.		inch			
Dim.			MAX.	MIN.	TYP.	MAX
А	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
В	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
С	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
н	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
L4 V2	0.60 0°		1.00 8°	0.024 0°		

TO-252 (DPAK) MECHANICAL DATA

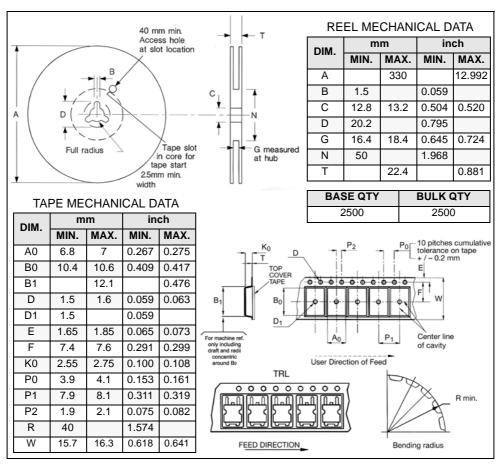


4 Packing Mechanical Data



DPAK FOOTPRINT

TAPE AND REEL SHIPMENT



5 Revision History

Date	Revision	Changes
17-Oct-2005	2	Inserted curves



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